

SGF40N60UF

Ultra-Fast IGBT

General Description

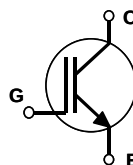
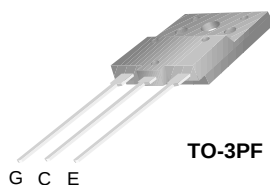
Fairchild's Insulated Gate Bipolar Transistor(IGBT) UF series provides low conduction and switching losses. UF series is designed for the applications such as motor control and general inverters where High Speed Switching is required.

Features

- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.1\text{ V @ } I_C = 20\text{ A}$
- High Input Impedance

Application

AC & DC Motor controls, General Purpose Inverters, Robotics, Servo Controls



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGF40N60UF	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	40	A
	Collector Current @ $T_C = 100^\circ\text{C}$	20	A
$I_{CM(1)}$	Pulsed Collector Current	160	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	100	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	40	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics of IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	600	--	--	V
ΔBV _{CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	--	0.6	--	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	250	μA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 100	nA

On Characteristics

V _{GE(th)}	G-E Threshold Voltage	I _C = 20mA, V _{CE} = V _{GE}	3.5	4.5	6.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 20A, V _{GE} = 15V	--	2.1	2.6	V
		I _C = 40A, V _{GE} = 15V	--	2.6	--	V

Dynamic Characteristics

C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	1430	--	pF
C _{oes}	Output Capacitance		--	170	--	pF
C _{res}	Reverse Transfer Capacitance		--	50	--	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time	V _{CC} = 300 V, I _C = 20A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	15	--	ns
t _r	Rise Time		--	30	--	ns
t _{d(off)}	Turn-Off Delay Time		--	65	130	ns
t _f	Fall Time		--	50	150	ns
E _{on}	Turn-On Switching Loss		--	160	--	μJ
E _{off}	Turn-Off Switching Loss	V _{CC} = 300 V, I _C = 20A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	200	--	μJ
E _{ts}	Total Switching Loss		--	360	600	μJ
t _{d(on)}	Turn-On Delay Time		--	30	--	ns
t _r	Rise Time		--	37	--	ns
t _{d(off)}	Turn-Off Delay Time		--	110	200	ns
t _f	Fall Time	V _{CE} = 300 V, I _C = 20A, V _{GE} = 15V	--	144	250	ns
E _{on}	Turn - On Switching Loss		--	310	--	μJ
E _{off}	Turn - Off Switching Loss		--	430	--	μJ
E _{ts}	Total Switching Loss		--	740	1200	μJ
Q _g	Total Gate Charge		--	97	150	nC
Q _{ge}	Gate-Emitter Charge	Measured 5mm from PKG	--	20	30	nC
Q _{gc}	Gate-Collector Charge		--	25	40	nC
L _e	Internal Emitter Inductance		--	14	--	nH

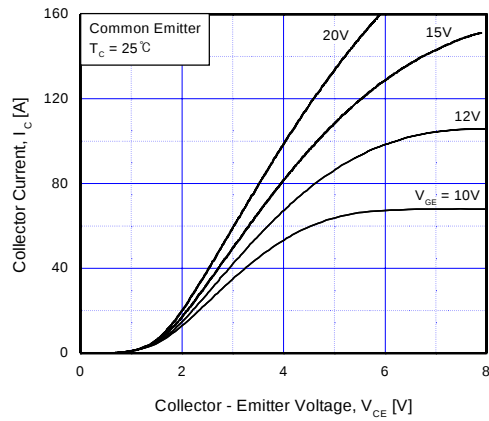


Fig 1. Typical Output Characteristics

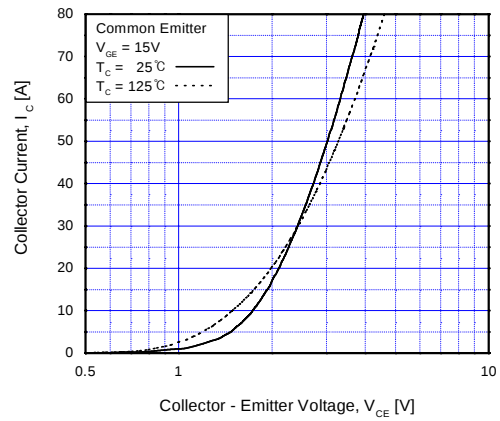


Fig 2. Typical Saturation Voltage Characteristics

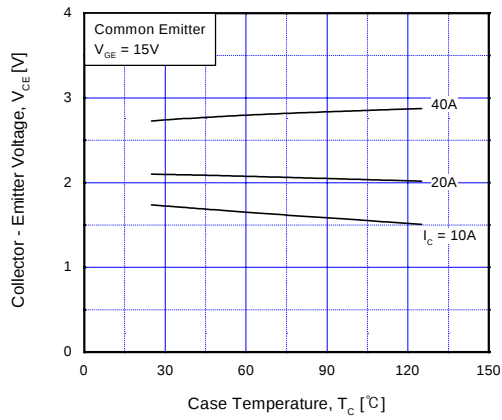


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

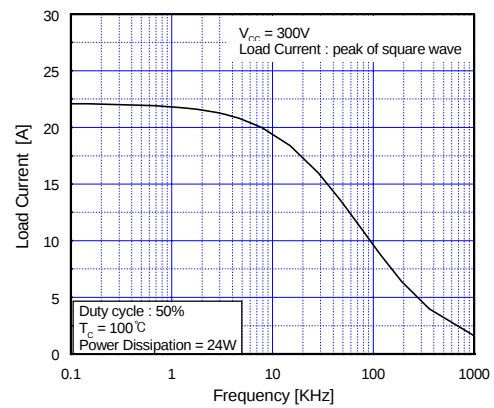
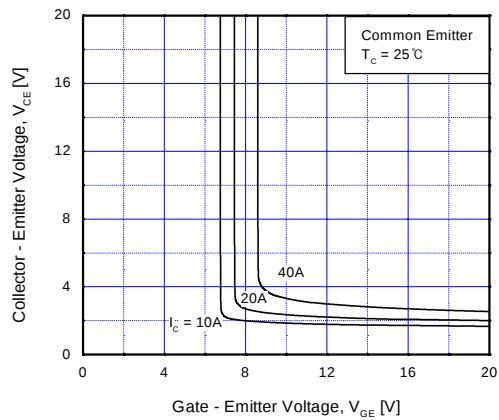
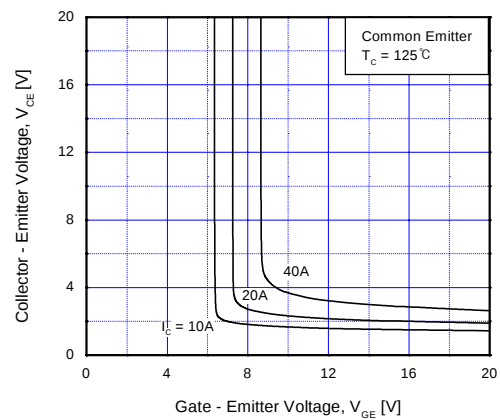


Fig 4. Load Current vs. Frequency

Fig 5. Saturation Voltage vs. V_{GE} Fig 6. Saturation Voltage vs. V_{GE}

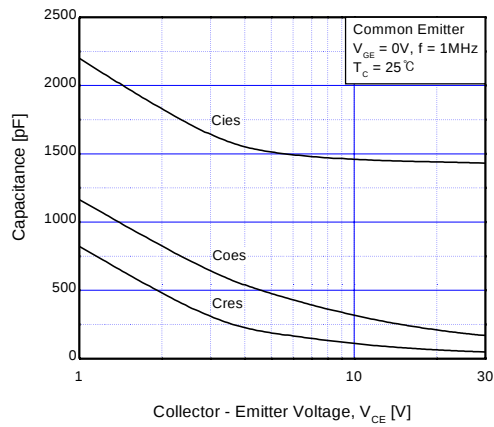


Fig 7. Capacitance Characteristics

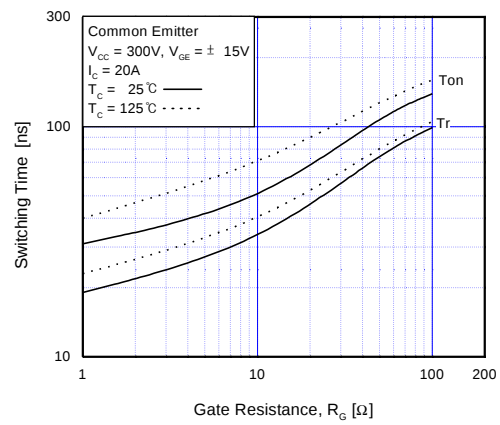


Fig 8. Turn-On Characteristics vs. Gate Resistance

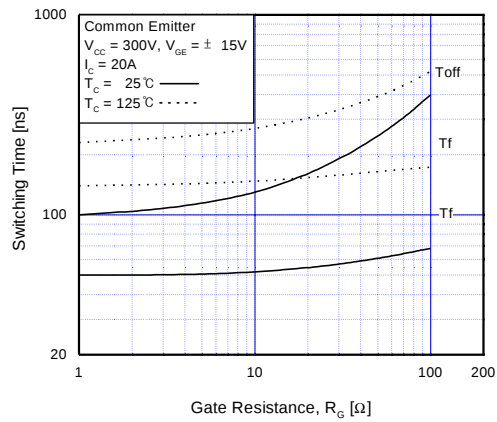


Fig 9. Turn-Off Characteristics vs. Gate Resistance

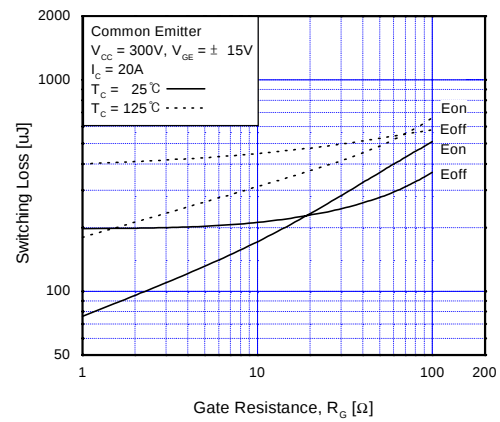


Fig 10. Switching Loss vs. Gate Resistance

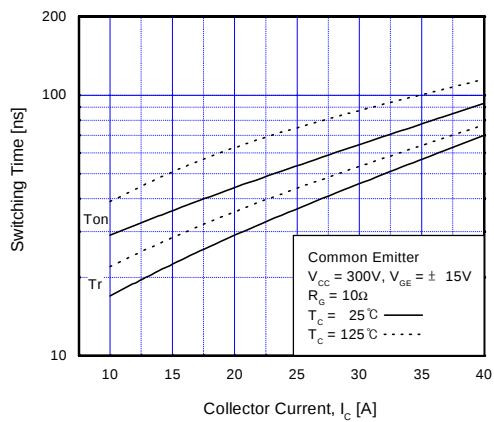


Fig 11. Turn-On Characteristics vs. Collector Current

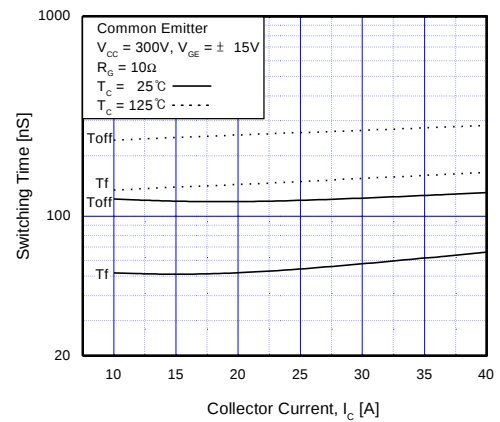


Fig 12. Turn-Off Characteristics vs. Collector Current

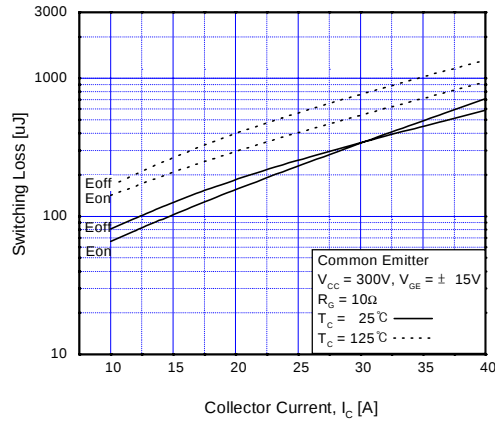


Fig 13. Switching Loss vs. Collector Current

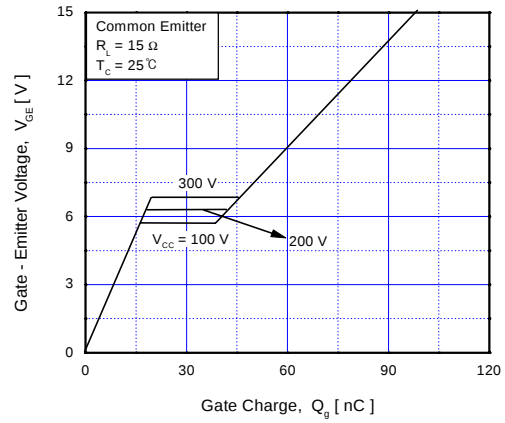


Fig 14. Gate Charge Characteristics

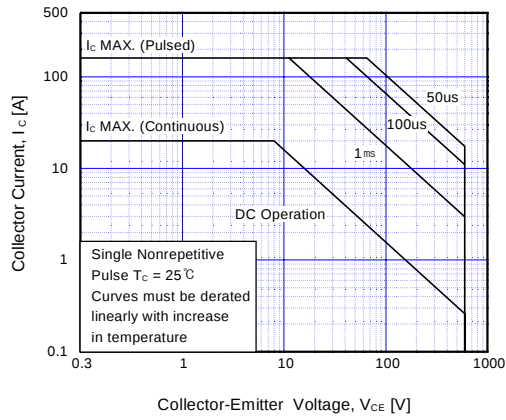


Fig 15. SOA Characteristics

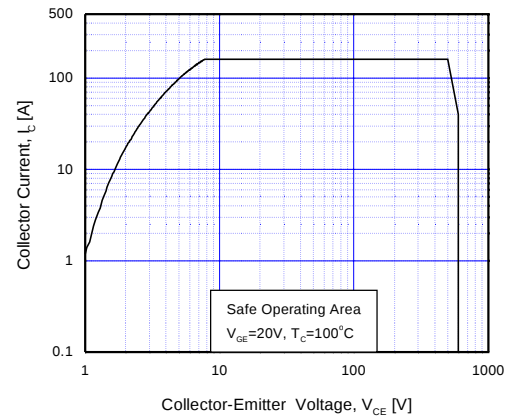


Fig 16. Turn-Off SOA Characteristics

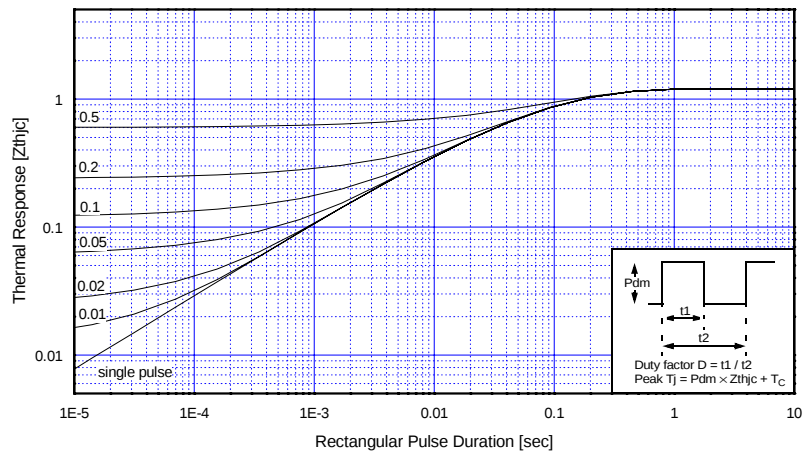
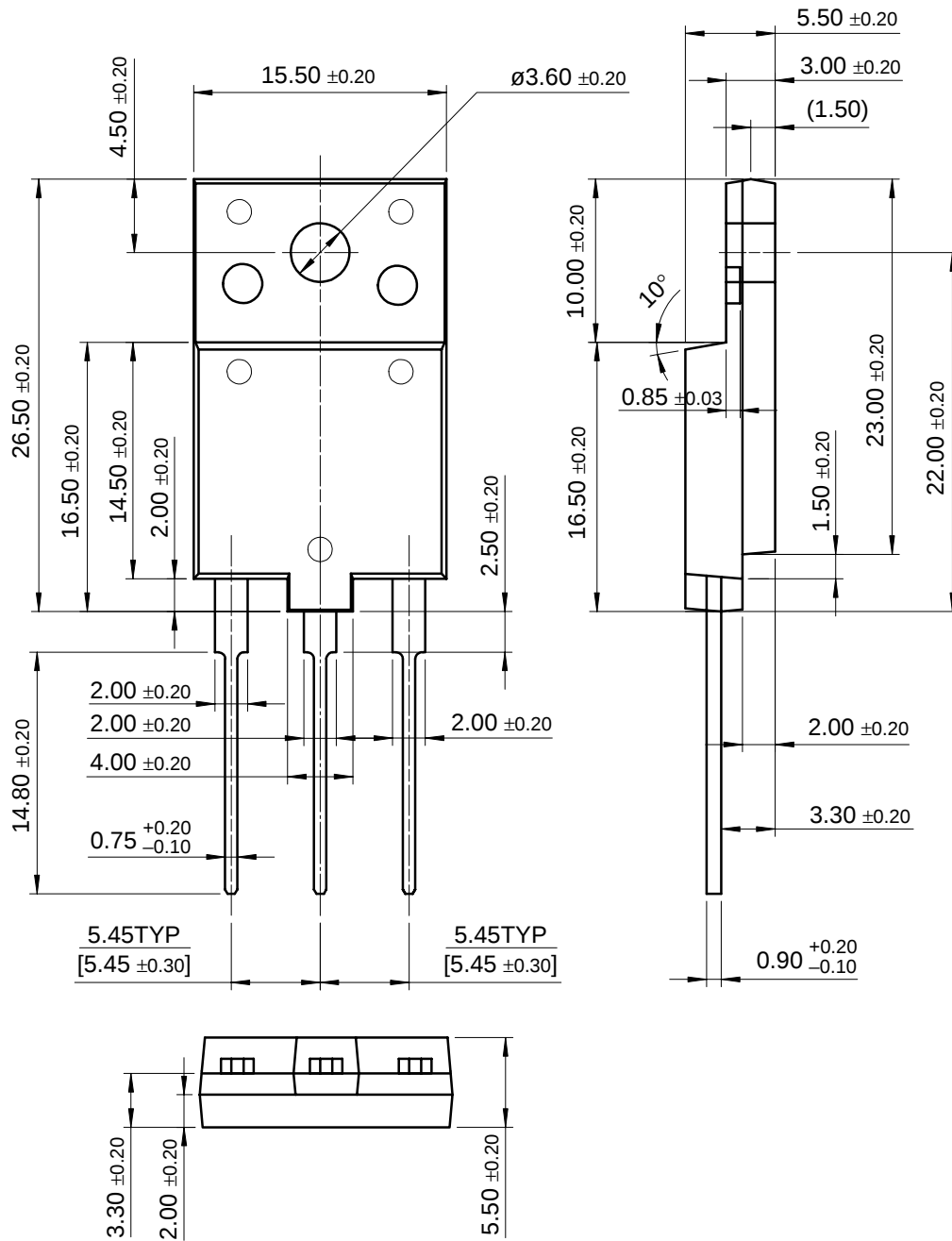


Fig 17. Transient Thermal Impedance of IGBT

Package Dimension

TO-3PF

SGF40N60UF



Dimensions in Millimeters

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